

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6588	257/66,190,200,210,758-760.ccls	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:06
L2	2	("5081053").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2004/11/09 12:06
L3	70	dielectric same ((cubic near boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:15
L4	1487	1 and "70"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:09
L5	3	1 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:16
L6	360760	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:10
L7	28	6 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:16
L8	267	dielectric and ((cubic near boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:15
L9	3	1 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:16
L10	96	6 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:16

S1	2510	composite near dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:53
S2	94	(composite near dielectric) and (effective near dielectric near constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 09:01
S3	2	((composite near dielectric) and (effective near dielectric near constant)) and (dielectric with ((cubic near boron near nitride) CBN))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/03 19:19
S4	33	(dielectric with ((cubic near boron near nitride) CBN))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/11/09 12:08
S5	2	("6674146").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2004/08/04 08:01
S6	1	"5081053".PN.	USPAT	OR	ON	2004/08/04 07:41
S7	5783	((contact near point\$1) gate junction interconnect\$3) near2 surface near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 08:04
S8	57	((((contact near point\$1) gate junction interconnect\$3) near2 surface near2 substrate) and ((boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 09:38
S9	49	composite near dielectric and ((boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:13
S10	791	dielectric with ((boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 08:59
S11	3	(dielectric with ((boron near nitride) CBN)) and (((contact near point\$1) gate junction interconnect\$3) near2 surface near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 08:59

S12	1331	dielectric same ((boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 08:59
S13	5	(dielectric same ((boron near nitride) CBN)) and (((contact near point\$1) gate junction interconnect\$3) near2 surface near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 08:59
S14	47	(dielectric same ((boron near nitride) CBN)) and (effective near dielectric near constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 09:01
S15	6	09/607,207	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 09:39
S16	8	dielectric near constant near Si3N4	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:50
S17	2	contact near composite near dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:51
S18	2	contact near through near2 composite near dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:52
S19	2	(contact near through near2 dielectric near (layer film)) and (composite near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:54
S20	194	contact near through near2 dielectric near (layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 12:05
S21	4	(contact near through near2 dielectric near (layer film)) and ((boron near nitride) CBN)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 11:55

S22	2	first near dielectric near surround\$3 near second near dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 12:08
S23	15	first near (insulat\$3 dielectric) near surround\$3 near second near (insulat\$3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 12:21
S24	0	first near (insulat\$3 dielectric) near2 ((boron near nitride) CBN) near surround\$3 near second near (insulat\$3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 12:20
S25	41	first near (insulat\$3 dielectric) near (cover\$3 surround\$3 around) near second near (insulat\$3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/08/04 12:21